IN THE CLAIMS

1. (Canceled).

2. (Previously Amended) The method of claim 3 wherein said semiconductor light emitter has at least one light extraction surface from where light is intended to be extracted, and wherein said forming is done on at least one extraction surface of said semiconductor light emitter.

3. (Currently Amended) A method of forming a light emitting device, said method comprising:

forming at least one of a Fresnel lens and a holographic diffuser on at least one surface of a semiconductor light emitter to affect light emitted by said semiconductor light emitter;

wherein said forming comprises pressing a stamping block against at least one surface of said semiconductor light emitter at an elevated temperature, said elevated temperature being higher than room temperature.

4. (Previously Amended) The method of claim 3 wherein said forming is executed concurrently with a wafer-bonding process, said wafer-bonding process comprising:

removing a first substrate of said semiconductor light emitter; and

bonding a second substrate to said semiconductor light emitter.

5. (Canceled).

6. (Reinstated and Currently Amended) The method of claim ~~1~~ 3 further comprising:

beveling one or more sides of said semiconductor light emitter.

7. (Reinstated and Currently Amended) The method of claim ~~1~~ 3 wherein said semiconductor light emitter has a light emitting layer, the method further comprising:

confining light emission to a preselected section of said light emitting layer.

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8. (Currently Amended) The method of claim ~~1~~ 3 wherein said semiconductor light emitter has a light emitting layer, the method further comprising confining light emission to a preselected section of said light emitting layer, wherein said confining comprises at least one method selected from applying the Holonyak process, using selective area growth, using selective area bonding, using diffusion, and using ion implantation.

9. (Previously Amended) The method of claim 3 further comprising:

coating one or more surfaces of said semiconductor light emitter with a reflective material.

10. (Previously Amended) The method of claim 3 further comprising:

coating said Fresnel lens or said holographic diffuser with a reflective material.

11. (Original) The method of claim 2 further comprising:

forming an optical element on the surface opposite of said extraction surface.

12-14. (Canceled).

15. (Reinstated and Currently Amended) The ~~device~~ method of claim ~~12 wherein~~ 27 further comprising beveling at least one surface of the semiconductor light ~~emitting device is beveled~~ emitter.

16. (Canceled).

17. (Reinstated and Currently Amended) The ~~device~~ method of claim ~~12~~ 45 wherein said semiconductor light emitter and said ~~first optical element~~ material comprise $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$.

18. (Reinstated and Currently Amended) The ~~device~~ method of claim ~~12~~ 45 wherein said semiconductor light ~~emitting diode~~ emitter comprises a III-nitride semiconductor alloy and said ~~first optical element~~ material comprises one of silicon carbide and sapphire.

19. (Reinstated and Currently Amended) The ~~device~~ method of claim ~~12~~ 45

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wherein said semiconductor light emitter and said ~~first optical element~~ material comprise aluminum gallium arsenide semiconductor alloy.

20. (Reinstated and Currently Amended) The ~~device~~ method of claim ~~12~~ 3, wherein said semiconductor light emitter has a flip-chip configuration.

21. (Reinstated and Currently Amended) The ~~device~~ method of claim ~~12~~ 3, wherein said semiconductor light emitter has a configuration in which a light emitting layer of said semiconductor light emitter is substantially perpendicular to said Fresnel lens or holographic diffuser.

22. (Canceled).

23. (Currently Amended) The ~~device~~ method of claim ~~12~~ 27, wherein said ~~first~~ optical element is designed to achieve one of light focusing, light collimating, and light diverging.

24. (Currently Amended) The ~~device~~ method of claim ~~12~~ 27, wherein said ~~first~~ optical element is designed to direct light in a preselected direction.

25. (Reinstated and Currently Amended) The ~~device~~ method of claim ~~12~~ 27 further comprising:

forming a second optical element on a surface of said semiconductor light emitter opposite the surface having said ~~first~~ optical element.

26. (Canceled).

27. (Currently Amended) A method of forming a light emitting device, said method comprising:

stamping at least one optical element on at least one surface of a semiconductor light emitter to affect the light emitted by said semiconductor light emitter;

wherein said stamping is executed at an elevated temperature, said elevated temperature being higher than room temperature.

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28. (Original) The method of claim 27 further comprising:

coating a surface of said light ~~emitting device~~ emitter with a reflective layer.

29. (Original) The method of claim 27 wherein said stamping is done on at least one of a semiconductor layer and a substrate layer of said semiconductor light emitter.

30. (Original) The method of claim 29 wherein said semiconductor layer comprises a transparent aluminum-bearing compound.

31. (Canceled).

32. (Currently Amended) The method of claim ~~31~~ 27, further comprising lowering said elevated temperature to facilitate the separation of a stamping block from said semiconductor light emitter after said stamping.

33. (Original) The method of claim 32, wherein said elevated temperature is higher than the ductile transition temperature of the material constituting said at least one surface on which said optical element is formed.

34-44. (Canceled).

45. (Currently Amended) A method for forming a light emitting device, said method comprising:

stamping an optical element in a material, said material being transparent to light emitted from said light emitting device, said material being one of high index optical glass, III-V semiconductors, II-VI semiconductors, group IV semiconductors, high-index organic semiconductors, high index organic compounds, and mixtures or alloys thereof; and

bonding said material to a semiconductor light emitter ;

wherein said stamping is executed at an elevated temperature, said elevated temperature being higher than room temperature.

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46. (Previously Added) The method of claim 45, wherein said stamping precedes said bonding.

47. (Previously Added) The method of claim 45, wherein said bonding precedes said stamping.

48-49. (Canceled).

50. (Previously Added) The method of claim 45, wherein bonding comprises bonding said material to a semiconductor light emitter with a bonding material, said bonding material being one of high index optical glass, III-V semiconductors, II-VI semiconductors, group IV semiconductors, high-index organic semiconductors, high index organic compounds, and mixtures or alloys thereof.

51. (Previously Added) The method of claim 45, wherein bonding comprises pressing said material together with said semiconductor light emitter at a temperature greater than room temperature.

52. (Canceled).

53. (New) The method of claim 3, further comprising providing an additional semiconductor light emitter to form an array of light emitting devices.

54. (New) The method of claim 3 wherein the semiconductor light emitter is a first semiconductor light emitter, the method further comprising:

providing a second semiconductor light emitter; and

providing a third semiconductor light emitter;

wherein one of the first, second, and third semiconductor light emitters emits red light; another of the first, second, and third semiconductor light emitters emits green light, and another of the first, second, and third semiconductor light emitters emits blue light.

55. (New) The method of claim 3 wherein:

the surface on which the at least one of Fresnel lens and holographic diffuser is formed comprises one of a III-arsenide material and a III-phosphide material; and

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the semiconductor light emitter comprises a light emitting layer comprising one of a III-arsenide material and a III-phosphide material.

56. (New) The method of claim 3 wherein:

the surface on which the at least one of Fresnel lens and holographic diffuser is formed comprises a III-nitride material; and

the semiconductor light emitter comprises a light emitting layer comprising a III-nitride material.

57. (New) The method of claim 27, further comprising providing an additional semiconductor light emitter to form an array of light emitting devices.

58. (New) The method of claim 27 wherein the semiconductor light emitter is a first semiconductor light emitter, the method further comprising:

providing a second semiconductor light emitter; and

providing a third semiconductor light emitter;

wherein one of the first, second, and third semiconductor light emitters emits red light; another of the first, second, and third semiconductor light emitters emits green light, and another of the first, second, and third semiconductor light emitters emits blue light.

59. (New) The method of claim 27 wherein:

the surface on which the at least one optical element is stamped comprises one of a III-arsenide material and a III-phosphide material; and

the semiconductor light emitter comprises a light emitting layer comprising one of a III-arsenide material and a III-phosphide material.

60. (New) The method of claim 27 wherein:

the surface on which the at least one optical element is stamped comprises a III-nitride material; and

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the semiconductor light emitter comprises a light emitting layer comprising a III-nitride material.

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